

# isc N-Channel MOSFET Transistor

# SPI20N60CFD

#### • FEATURES

- Static drain-source on-resistance:
  R<sub>DS</sub>(on) ≤0.22Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRIPTION

- · Ultra low gate charge
- High peak current capability

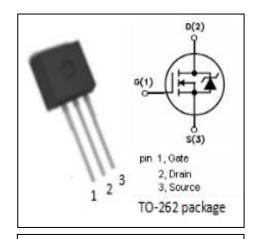


• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	600	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous 20.7		А
Ірм	Drain Current-Single Pulsed	52	А
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	208	W
Tj	Max. Operating Junction Temperature	150	${\mathbb C}$
T <sub>stg</sub>	Storage Temperature	-55~150	${\mathbb C}$

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT			
Rth(ch-c)	Channel-to-case thermal resistance	0.6	°C/W			



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	DIM	MIN	MAX	
	A	4.37	4.77	
	A1	1. 22	1.42	
	A2	2.47	2.87	
	Ъ	0.70	0.97	
	Ъ2	1.17	1.42	
	С	0.28	0.53	
	D	23.20	24.02	
	D1	8.38	8.90	
	D2	6.00	-8	
	E	9.90	10.39	
	E4	7.30		
	е	1000	4BSC	
	G	1.25	1.50	
	H2	1 N <del>ex</del>	1.31	
	L	13.34	14.10	
	T 1	3.30	4.06	
	L1 L3	0.95	1.15	



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID =0.25mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID =1mA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; ID=13.1A			0.22	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =20V; V <sub>DS</sub> =0V			0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V		2.1		μА
$V_{SD}$	Diode forward voltage	I <sub>F</sub> =Is; V <sub>GS</sub> = 0V			1.2	V

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